	Type	Hits	Search T xt
1	BRS	65956	eprom or eeprom or electronic$4 adj program$6
2	BRS	58465	gate near2 (oxide or nitride or dielectric or insulator)
3	BRS	148551	mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet
4	BRS	151178	((mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) or transistor) near2 (switch$4 or control$4 or periph$6)
5	BRS	0	(eprom or eeprom or electronic$4 adj program$6) near8 (gate near2 (oxide or nitride or dielectric or insulator)) near8 (((mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) or transistor) near2 (switch$4 or control$4 or periph$6)) near8 (simultan$4 or "same time")
6	BRS	7	(eprom or eeprom or electronic$4 adj program$6) same (gate near2 (oxide or nitride or dielectric or insulator)) same (((mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) or transistor) near2 (switch$4 or control$4 or periph$6)) same (simultan$4 or "same time")
7	BRS	2	4835740.pn.
8	BRS	26	4835740.uref.
9	BRS	21734	floating adj gate
10	BRS	198	(floating adj gate) near8 gate adj electrode near8 (simultaneous$4 or together or "same time")
11	BRS	149	((floating adj gate) near8 gate adj electrode near8 (simultaneous$4 or together or "same time")) and (@ay < "2000")

	DBs
1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
7	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
8	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
9	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
10	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
11	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

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	Type	Hits	S arch Text
12	BRS	4107439	switch$4 or controling or controlling or periph$6
13	BRS	187	(form$4 or etch$4) near4 (floating adj gate) near4 (switch$4 or controling or controlling or periph$6)
14	BRS	160	((form$4 or etch$4) near4 (floating adj gate) near4 (switch$4 or controling or controlling or periph$6)) and (@ay < "2000"
15	BRS	157	(((form$4 or etch$4) near4 (floating adj gate) near4 (switch$4 or controling or controlling or periph$6)) and (@ay < "2000")) not ((((floating adj gate) near8 gate adj electrode near8 (simultaneous$4 or together or "same time")) and (@ay < "2000"))
16	BRS	58465	gate near2 (oxide or nitride or dielectric or insulator)
17	BRS	4935	(peripher$4 or logic$4) near4 (vpp or high-volt$4 or high adj volt$4)
18	BRS	6854	(peripher$4 or logic$4) near8 (vpp or high-volt$4 or high adj volt$4)
19	BRS	148643	thick$6 near4 ("same" or equivalent or equivalant or equal)
20	BRS	12	(gate near2 (oxide or nitride or dielectric or insulator)) same ((peripher$4 or logic$4) near8 (vpp or high-volt$4 or high adj volt$4)) same (thick$6 near4 ("same" or equivalent or equivalant or equal))

	DBs
12	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
13	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
14	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
15	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
16	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
17	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
18	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
19	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
20	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

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